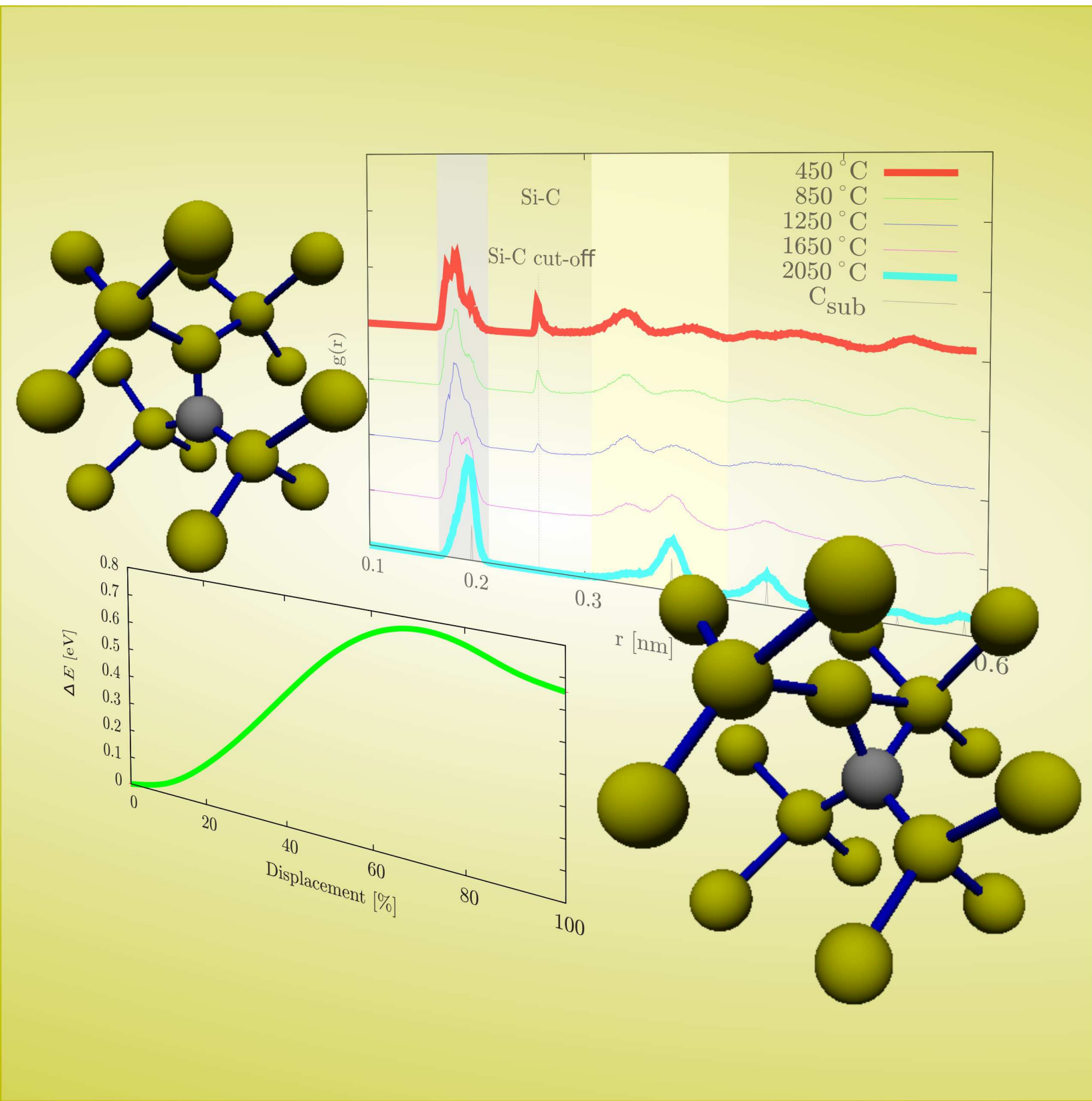
Si-C
Si-C cut-off
450 °C
850 °C
1250 °C
1650 °C
2050 °C
C_sub
g(r)
0.1
0.2
0.3
0.6
r [nm]
ΔE [eV]
0.8
0.7
0.6
0.5
0.4
0.3
0.2
0.1
0
0
20
40
60
80
100
Displacement [%]